

# MOSFET – Power, Single N-Channel

## 40 V, 1.39 mΩ, 386 A

### NVMJST1D3N04C

#### Features

- Small Footprint (5x7 mm) for Compact Design
- Low  $R_{DS(on)}$  to Minimize Conduction Losses
- Low  $Q_G$  and Capacitance to Minimize Driver Losses
- TCPAK57 5x7 Top Cool Package
- AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

#### MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

| Parameter                                                                    | Symbol                                         | Value                     | Unit             |
|------------------------------------------------------------------------------|------------------------------------------------|---------------------------|------------------|
| Drain-to-Source Voltage                                                      | $V_{DSS}$                                      | 40                        | V                |
| Gate-to-Source Voltage                                                       | $V_{GS}$                                       | $\pm 20$                  | V                |
| Continuous Drain Current $R_{\theta JC}$ (Notes 1, 3)                        | Steady State                                   | $T_C = 25^\circ\text{C}$  | $I_D$ 386 A      |
|                                                                              |                                                | $T_C = 100^\circ\text{C}$ | 273              |
| Power Dissipation $R_{\theta JC}$ (Note 1)                                   | Steady State                                   | $T_C = 25^\circ\text{C}$  | $P_D$ 375 W      |
|                                                                              |                                                | $T_C = 100^\circ\text{C}$ | 187              |
| Pulsed Drain Current                                                         | $T_A = 25^\circ\text{C}, t_p = 10 \mu\text{s}$ | $I_{DM}$ 900              | A                |
| Operating Junction and Storage Temperature Range                             | $T_J, T_{stg}$                                 | -55 to +175               | $^\circ\text{C}$ |
| Source Current (Body Diode)                                                  | $I_S$                                          | 312                       | A                |
| Single Pulse Drain-to-Source Avalanche Energy ( $I_{L(pk)} = 19 \text{ A}$ ) | $E_{AS}$                                       | 739                       | mJ               |
| Lead Temperature for Soldering Purposes (1/8" from case for 10 s)            | $T_L$                                          | 260                       | $^\circ\text{C}$ |

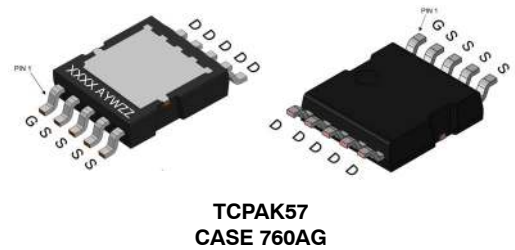
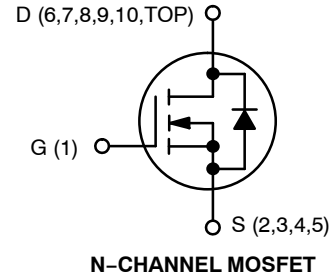
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

#### THERMAL RESISTANCE MAXIMUM RATINGS

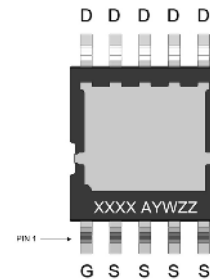
| Parameter                                   | Symbol          | Value | Unit                      |
|---------------------------------------------|-----------------|-------|---------------------------|
| Junction-to-Case – Steady State             | $R_{\theta JC}$ | 0.4   | $^\circ\text{C}/\text{W}$ |
| Junction-to-Ambient – Steady State (Note 2) | $R_{\theta JA}$ | 29.2  |                           |
| Junction-to-Heatsink Top (Note 2)           | $\Psi_{JH}$     | 1.67  |                           |
| Junction-to-Drain Lead                      | $\Psi_{JL}$     | 5.4   |                           |
| Junction-to-Source Lead                     | $\Psi_{JL}$     | 5.3   |                           |

1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. 2s2p JEDEC51-7 standard PCB mounted to a 25x25x3 (mm) aluminum heatsink with a 12 w/mK TIM interface.
3. Maximum current for pulses as long as 1 second is higher but is dependent on pulse duration and duty cycle.

| $V_{(BR)DSS}$ | $R_{DS(ON) MAX}$ | $I_D MAX$ |
|---------------|------------------|-----------|
| 40 V          | 1.39 mΩ @ 10 V   | 386 A     |



#### MARKING DIAGRAM



- XXXX = Specific Device Code
- A = Assembly Location
- Y = Year
- W = Work Week
- ZZ = Assembly Lot

#### ORDERING INFORMATION

See detailed ordering, marking and shipping information in the package dimensions section on page 5 of this data sheet.

# NVMJST1D3N04C

## ELECTRICAL CHARACTERISTICS (T<sub>J</sub> = 25°C unless otherwise specified)

| Parameter | Symbol | Test Condition | Min | Typ | Max | Unit |
|-----------|--------|----------------|-----|-----|-----|------|
|-----------|--------|----------------|-----|-----|-----|------|

### OFF CHARACTERISTICS

|                                                           |                                      |                                                  |                        |     |     |       |
|-----------------------------------------------------------|--------------------------------------|--------------------------------------------------|------------------------|-----|-----|-------|
| Drain-to-Source Breakdown Voltage                         | V <sub>(BR)DSS</sub>                 | V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA   | 40                     |     |     | V     |
| Drain-to-Source Breakdown Voltage Temperature Coefficient | V <sub>(BR)DSS</sub> /T <sub>J</sub> |                                                  |                        | 9.6 |     | mV/°C |
| Zero Gate Voltage Drain Current                           | I <sub>DSS</sub>                     | V <sub>GS</sub> = 0 V,<br>V <sub>DS</sub> = 40 V | T <sub>J</sub> = 25°C  |     | 10  | μA    |
|                                                           |                                      |                                                  | T <sub>J</sub> = 125°C |     | 100 |       |
| Gate-to-Source Leakage Current                            | I <sub>GSS</sub>                     | V <sub>DS</sub> = 0 V, V <sub>GS</sub> = 20 V    |                        |     | 100 | nA    |

### ON CHARACTERISTICS (Note 4)

|                                   |                                     |                                                             |     |      |      |       |
|-----------------------------------|-------------------------------------|-------------------------------------------------------------|-----|------|------|-------|
| Gate Threshold Voltage            | V <sub>GS(TH)</sub>                 | V <sub>GS</sub> = V <sub>DS</sub> , I <sub>D</sub> = 170 μA | 2.5 |      | 3.5  | V     |
| Threshold Temperature Coefficient | V <sub>GS(TH)</sub> /T <sub>J</sub> |                                                             |     | -8.6 |      | mV/°C |
| Drain-to-Source On Resistance     | R <sub>DS(on)</sub>                 | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 50 A               |     | 1.2  | 1.39 | mΩ    |
| Forward Transconductance          | g <sub>FS</sub>                     | V <sub>DS</sub> = 15 V, I <sub>D</sub> = 50 A               |     | 145  |      | S     |

### CHARGES AND CAPACITANCES

|                              |                     |                                                                       |  |      |  |    |
|------------------------------|---------------------|-----------------------------------------------------------------------|--|------|--|----|
| Input Capacitance            | C <sub>ISS</sub>    | V <sub>GS</sub> = 0 V, f = 1 MHz, V <sub>DS</sub> = 25 V              |  | 4300 |  | pF |
| Output Capacitance           | C <sub>OSS</sub>    |                                                                       |  | 2100 |  |    |
| Reverse Transfer Capacitance | C <sub>RSS</sub>    |                                                                       |  | 59   |  |    |
| Total Gate Charge            | Q <sub>G(TOT)</sub> | V <sub>GS</sub> = 10 V, V <sub>DS</sub> = 20 V; I <sub>D</sub> = 50 A |  | 65   |  | nC |
| Threshold Gate Charge        | Q <sub>G(TH)</sub>  | V <sub>GS</sub> = 10 V, V <sub>DS</sub> = 20 V; I <sub>D</sub> = 50 A |  | 13   |  |    |
| Gate-to-Source Charge        | Q <sub>GS</sub>     |                                                                       |  | 20   |  |    |
| Gate-to-Drain Charge         | Q <sub>GD</sub>     |                                                                       |  | 12   |  |    |
| Plateau Voltage              | V <sub>GP</sub>     |                                                                       |  | 4.7  |  | V  |

### SWITCHING CHARACTERISTICS (Note 5)

|                     |                     |                                                                                                  |  |     |  |    |
|---------------------|---------------------|--------------------------------------------------------------------------------------------------|--|-----|--|----|
| Turn-On Delay Time  | t <sub>d(ON)</sub>  | V <sub>GS</sub> = 10 V, V <sub>DS</sub> = 20 V,<br>I <sub>D</sub> = 50 A, R <sub>G</sub> = 2.5 Ω |  | 15  |  | ns |
| Rise Time           | t <sub>r</sub>      |                                                                                                  |  | 47  |  |    |
| Turn-Off Delay Time | t <sub>d(OFF)</sub> |                                                                                                  |  | 36  |  |    |
| Fall Time           | t <sub>f</sub>      |                                                                                                  |  | 9.0 |  |    |

### DRAIN-SOURCE DIODE CHARACTERISTICS

|                         |                 |                                                                                 |                        |    |      |     |    |
|-------------------------|-----------------|---------------------------------------------------------------------------------|------------------------|----|------|-----|----|
| Forward Diode Voltage   | V <sub>SD</sub> | V <sub>GS</sub> = 0 V,<br>I <sub>S</sub> = 50 A                                 | T <sub>J</sub> = 25°C  |    | 0.82 | 1.2 | V  |
|                         |                 |                                                                                 | T <sub>J</sub> = 125°C |    | 0.68 |     |    |
| Reverse Recovery Time   | t <sub>RR</sub> | V <sub>GS</sub> = 0 V, dI <sub>S</sub> /dt = 100 A/μs,<br>I <sub>S</sub> = 50 A |                        | 63 |      | ns  |    |
| Charge Time             | t <sub>a</sub>  |                                                                                 |                        | 34 |      |     |    |
| Discharge Time          | t <sub>b</sub>  |                                                                                 |                        | 29 |      |     |    |
| Reverse Recovery Charge | Q <sub>RR</sub> |                                                                                 |                        | 92 |      |     | nC |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.

5. Switching characteristics are independent of operating junction temperatures.

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## TYPICAL CHARACTERISTICS

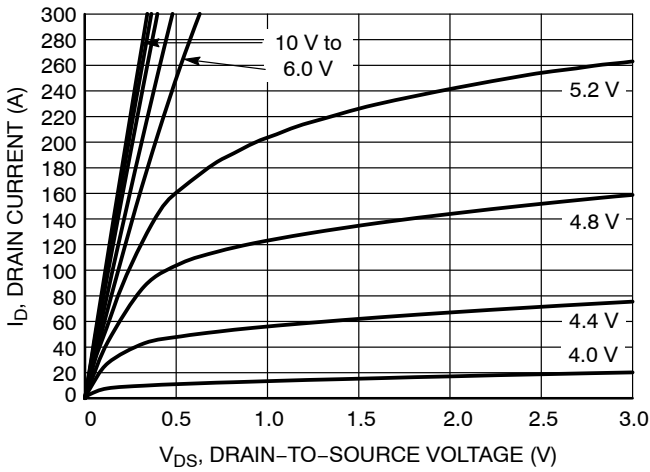


Figure 1. On-Region Characteristics

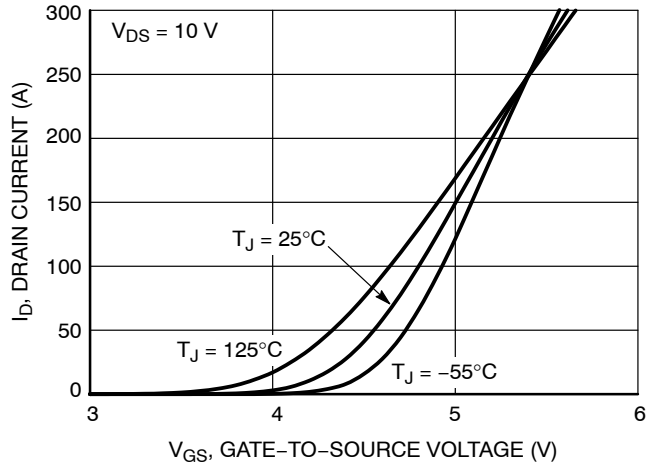


Figure 2. Transfer Characteristics

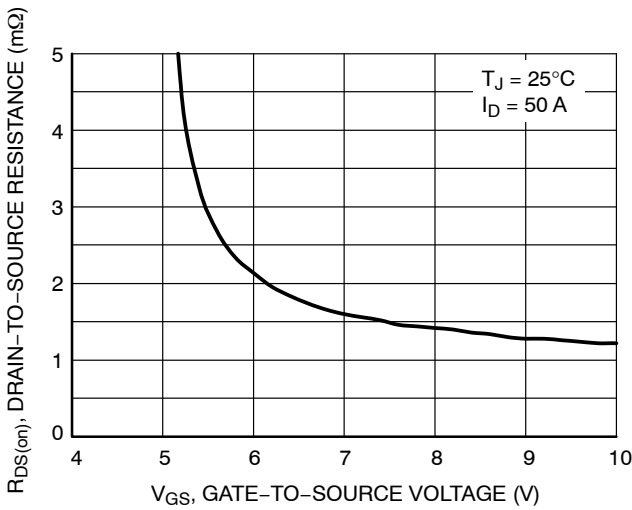


Figure 3. On-Resistance vs. Gate-to-Source Voltage

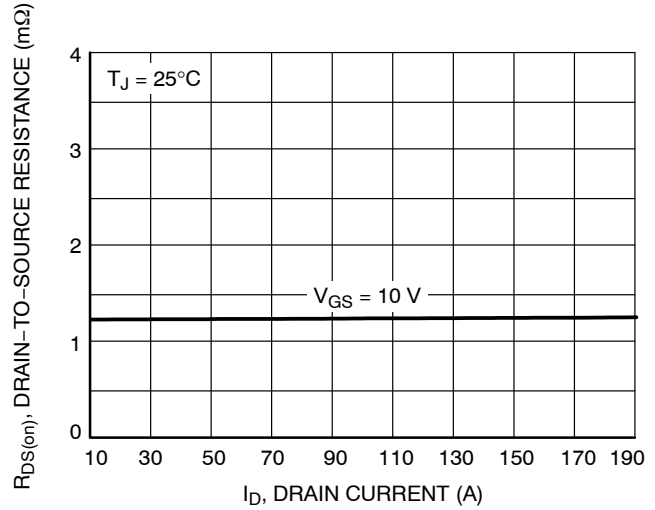


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

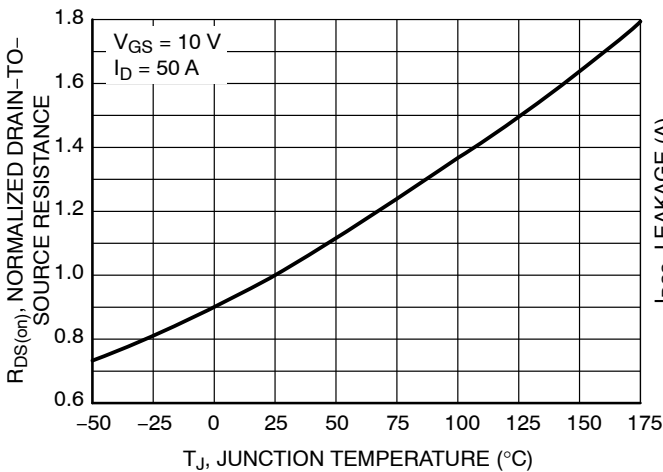


Figure 5. On-Resistance Variation with Temperature

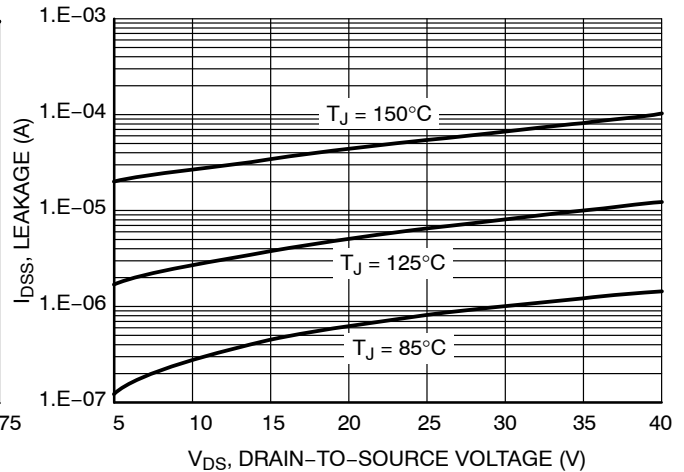


Figure 6. Drain-to-Source Leakage Current vs. Voltage

# NVMJST1D3N04C

## TYPICAL CHARACTERISTICS

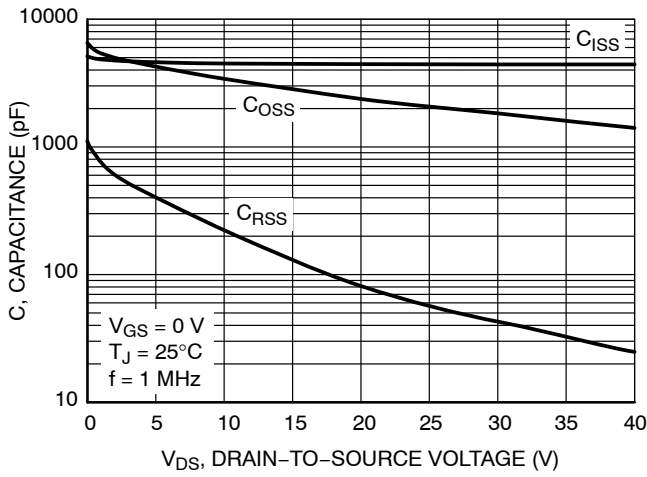


Figure 7. Capacitance Variation

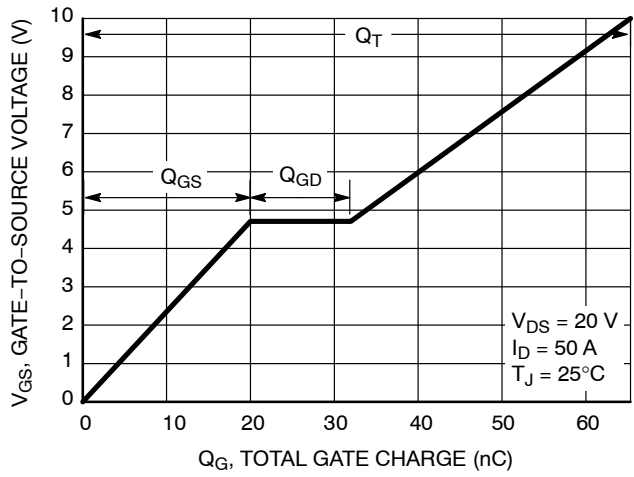


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

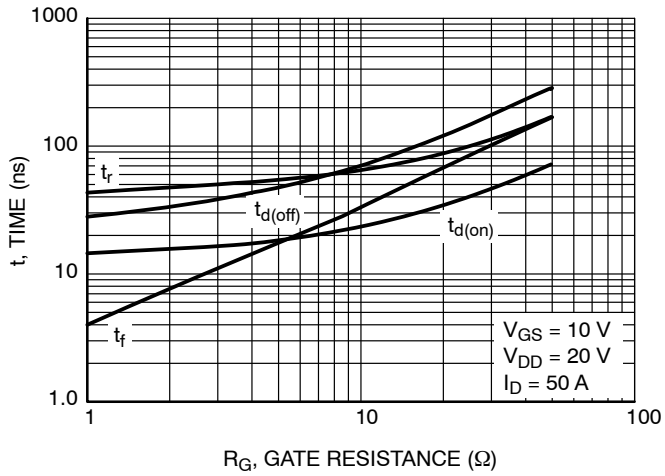


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

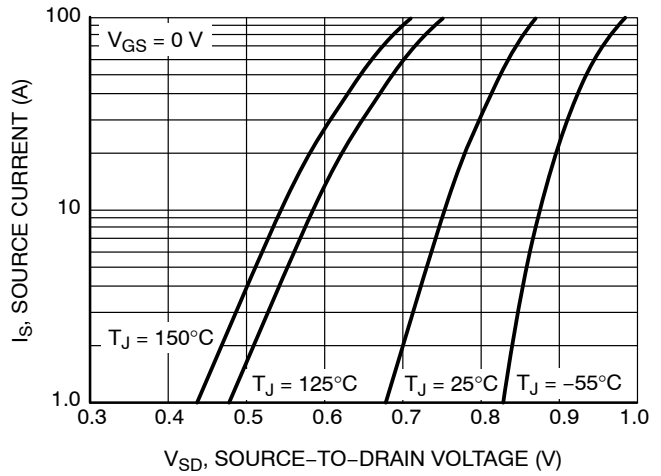


Figure 10. Diode Forward Voltage vs. Current

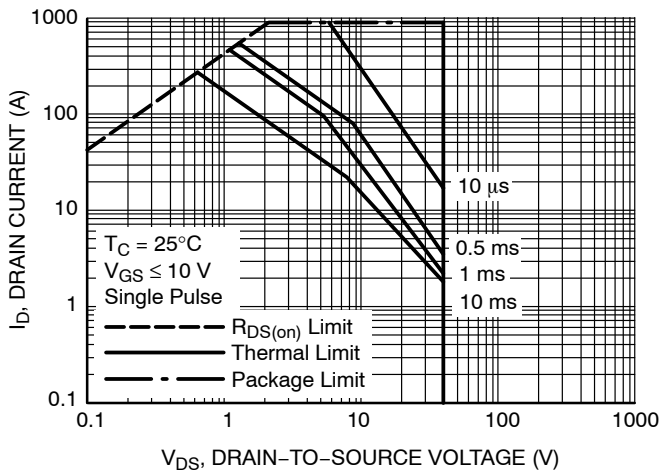


Figure 11. Safe Operating Area

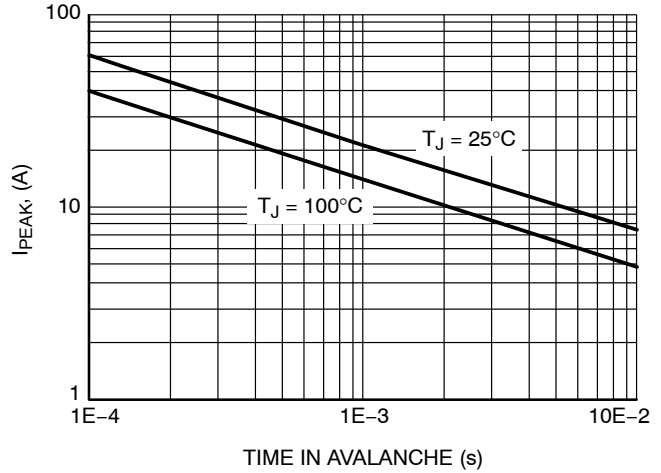


Figure 12.  $I_{PEAK}$  vs. Time in Avalanche

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## TYPICAL CHARACTERISTICS

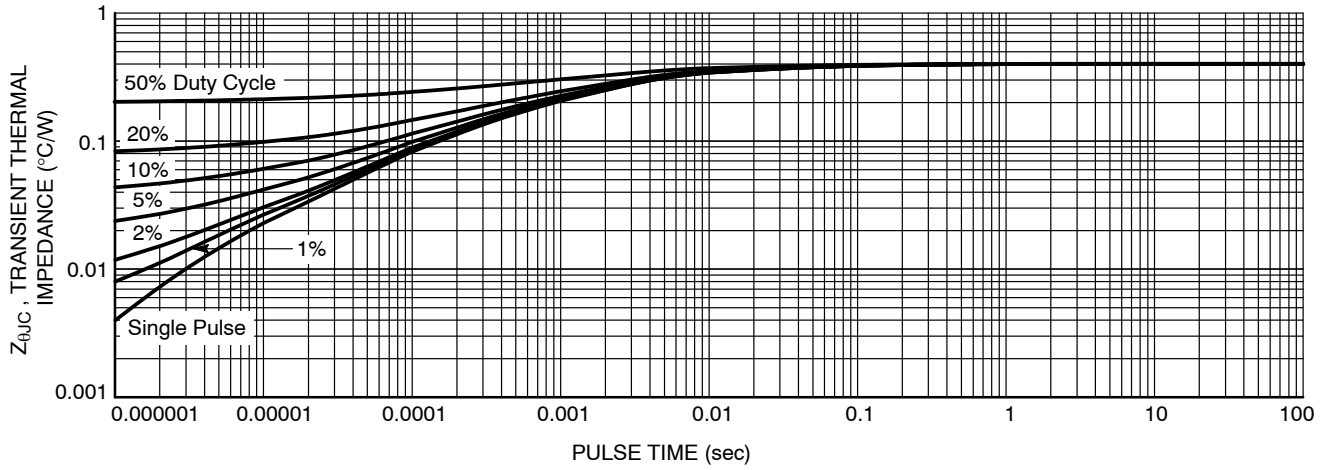


Figure 13. Thermal Characteristics

### DEVICE ORDERING INFORMATION

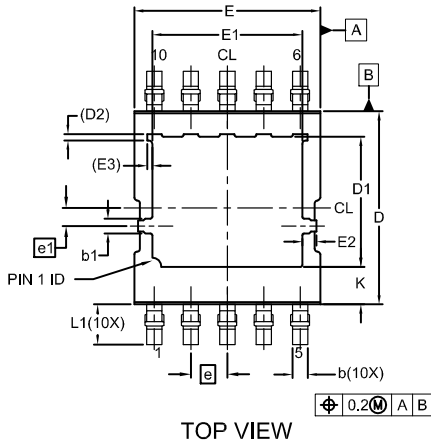
| Device           | Marking | Package                       | Shipping <sup>†</sup> |
|------------------|---------|-------------------------------|-----------------------|
| NVMJST1D3N04CTXG | 1D34C   | TCPAK57 Top Cool<br>(Pb-Free) | 3000 / Tape & Reel    |

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

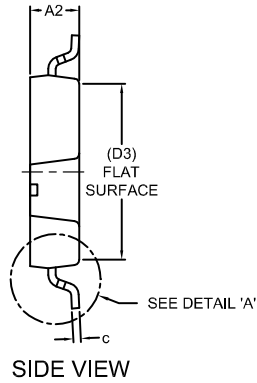
# NVMJST1D3N04C

## PACKAGE DIMENSIONS

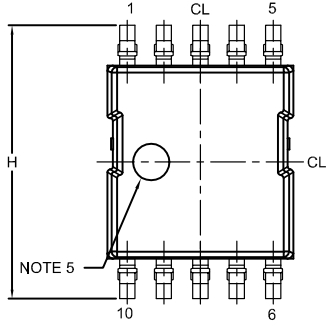
### LFLPAK10 7.5x5 CASE 760AG ISSUE C



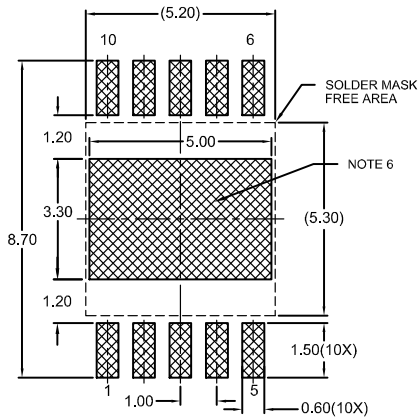
TOP VIEW



SIDE VIEW



BOTTOM VIEW



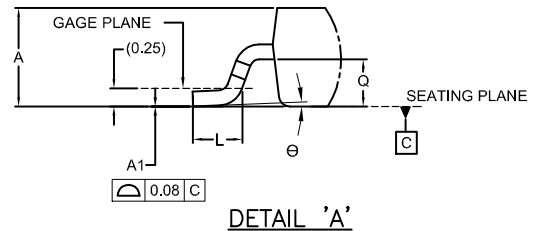
LAND PAD RECOMMENDATION

\*FOR ADDITIONAL INFORMATION ON OUR PB-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

#### NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. UNIT DIMENSION: MILLIMETERS
3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH PROTRUSIONS OR GATE BURRS SHALL NOT EXCEED 0.150mm PER SIDE.
4. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY. OPTIONAL MOLD FEATURE.
5. LAND PAD UNDER THE PACKAGE BODY IS FOR MECHANICAL SUPPORT ONLY. SOLDER CONNECTION IS NOT REQUIRED.
7. DIMENSION A1 IS THE LEAD STAND-OFF FROM THE BOTTOM SURFACE OF THE PACKAGE BODY.

| MILLIMETERS |          |      |      |
|-------------|----------|------|------|
| DIM         | MIN      | NOM  | MAX  |
| A           | 1.30     | 1.35 | 1.45 |
| A1          | -0.05    | 0.00 | 0.05 |
| A2          | 1.30     | 1.35 | 1.40 |
| b           | 0.36     | 0.41 | 0.46 |
| b1          | 0.30     | 0.40 | 0.50 |
| c           | 0.16     | 0.21 | 0.26 |
| D           | 5.20     | 5.30 | 5.40 |
| D1          | 3.47     | 3.57 | 3.67 |
| D2          | 0.17 REF |      |      |
| D3          | 4.82 REF |      |      |
| E           | 5.00     | 5.10 | 5.20 |
| E1          | 4.02     | 4.12 | 4.22 |
| E2          | 0.30     | 0.40 | 0.50 |
| E3          | 0.14 REF |      |      |
| e           | 1.00 BSC |      |      |
| e1          | 0.50 BSC |      |      |
| K           | 0.93     | 1.03 | 1.13 |
| H           | 7.30     | 7.50 | 7.70 |
| L           | 0.49     | 0.69 | 0.89 |
| L1          | 0.90     | 1.10 | 1.30 |
| Q           | 0.60     | 0.65 | 0.70 |
| Θ           | 0°       | 2.5° | 5°   |



DETAIL 'A'

# NVMJST1D3N04C

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